AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

Claims 1-13 (Cancelled).

14. (Currently Amended) A rectifier system, comprising:

a rectifier bridge for a three-phase generator, the rectifier bridge including a plurality of rectifier elements, wherein at least some of the rectifier elements are different from others of the rectifier elements in at least one property;

wherein the rectifier elements have properties selected in such a way that one of: i) ripple of a voltage which can be picked off an the output of the rectifier system is minimal or ii) ripple of a current which can be picked off at the output of the rectified system is minimal.

15. (Canceled).

16. (Currently Amended) ~~The rectifier system as recited in claim 14,~~ A rectifier system, comprising:

a rectifier bridge for a three-phase generator, the rectifier bridge including a plurality of rectifier elements, wherein at least some of the rectifier elements are different from others of the rectifier elements in at least one property;

wherein the at least one property is at least one of: i) a switching time, ii) a reverse recovery switching time, iii) a current density, iv) a chip area, v) a chip thickness, vi) a breakdown voltage, vii) an internal resistance, viii) a path resistance, and ix) another property which is suited for reducing ripple.

17. (Previously Presented) The rectifier system as recited in claim 14, wherein the rectifier elements are diodes.

18. (Previously Presented) The rectifier system as recited in claim 17, wherein the diodes are Zener diodes.

19. (Previously Presented) The rectifier system as recited in claim 14, wherein the at least some of the rectifier elements are parallel connections of two diodes having different properties.

20. (Previously Presented) The rectifier system as recited in claim 19, wherein the two diodes have, relative to each other, one of different switching times or different reverse recovery switching times.

21. (Previously Presented) The rectifier system as recited in claim 19, wherein the two diodes have different reverse recovery switching times, the different reverse recovery switching times being achieved by using diodes having different breakdown voltages.

22. (Previously Presented) The rectifier system as recited in claim 21, wherein one of the two diodes is in a Zener voltage range of 18 volts through 50 volts and the other of the two diodes is in a Zener voltage range of 100 volts through 800 volts.

23. (Previously Presented) The rectifier system as recited in claim 21, wherein the at least one property includes different current densities, the different current density of the rectifier elements being implemented through different at least one of: i) chip areas, ii) chip thicknesses, and iii) path resistances.

24. (Previously Presented) The rectifier system as recited in claim 14, wherein the rectifier elements in the rectifier bridge include twelve diodes, pairs of the twelve diodes having different properties and being connected in parallel.

25. (Previously Presented) The rectifier system as recited in claim 14, wherein the rectifier elements in the rectifier bridge include twelve diodes, pairs of the diodes being connected in parallel, only positive pairs of diodes having different properties relative to one another.

26. (Previously Presented) The rectifier system as recited in claim 14, wherein the rectifier elements in the rectified bridge include twelve diodes, pairs of the diodes being connected in parallel, only negative pairs of diodes having different properties relative to one another.

27. (Previously Presented) The rectifier system as recited in claim 14, wherein the rectifier elements in the rectifier bridge include twelve diodes, four of the diodes having a first property and eight diodes having a second property, the first and second properties being different from one another.

28. (Previously Presented) The rectifier system as recited in claim 14, wherein the rectifier bridge has nine diodes.